

V_{RRM} = 650 V
 $I_F (T_C=160^\circ\text{C})$ = 6 A
 Q_C = 17 nC

Features

- Extremely low reverse current
- No reverse recovery current
- Temperature independent switching
- Positive temperature coefficient on V_F
- Excellent surge current capability
- Low capacitive charge

Benefits

- Essentially no switching losses
- System efficiency improvement over Si diodes
- Increased power density
- Enabling higher switching frequency
- Reduction of heat sink requirements
- System cost savings due to smaller magnetics
- Reduced EMI

Applications

- Switch mode power supplies (SMPS)
- Uninterruptible power supplies
- Motor drivers
- Power factor correction

Package Pin Definitions

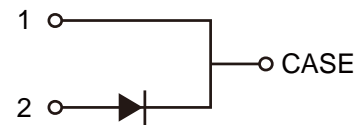
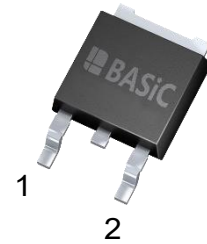
- Pin1- Cathode
- Pin2- Anode

Package Parameters

| Part Number | Marking | Package |
|-------------|-----------|----------|
| B2D06065E | B2D06065E | TO-252-2 |

TO-252-2

CASE



Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Test conditions | Value | Unit |
|---------------|--------------------------------------|---|-----------|------------------|
| V_{RRM} | Repetitive peak reverse voltage | | 650 | V |
| V_{RSM} | Non-repetitive peak reverse voltage | | 650 | V |
| I_F | Continuous forward current | $T_c=25^\circ\text{C}$ $T_c=160^\circ\text{C}$ | 24 6 | A |
| I_{FSM} | Non-Repetitive forward surge current | $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Wave | 48 | A |
| $\int i^2 dt$ | i^2t value | $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$ | 11.52 | A ² S |
| P_{tot} | Power dissipation | $T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$ | 107 46 | W |
| T_j | Operating junction temperature | | -55~175 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature | | -55~175 | $^\circ\text{C}$ |

Thermal Characteristics

| Symbol | Parameter | Value | | | Unit |
|--------------|--|-------|-------|------|------|
| | | Min. | Typ. | Max. | |
| $R_{th(jc)}$ | Thermal resistance from junction to case | | 1.401 | | K/W |

Electrical Characteristics
Static Characteristics

| Symbol | Parameter | Test conditions | Value | | | Unit |
|----------|-----------------------|---|-------|--------------|------|---------|
| | | | Min. | Typ. | Max. | |
| V_{DC} | DC blocking voltage | $T_j=25^{\circ}C$ | 650 | | | V |
| V_F | Diode forward voltage | $I_F=6A$ $T_j=25^{\circ}C$ $I_F=6A$ $T_j=175^{\circ}C$ | | 1.33 1.63 | | V |
| I_R | Reverse current | $V_R=650V$ $T_j=25^{\circ}C$ $V_R=650V$ $T_j=175^{\circ}C$ | | 1 15 | | μA |

AC Characteristics

| Symbol | Parameter | Test conditions | Value | | | Unit |
|--------|---------------------------|---|-------|---------------------|------|---------|
| | | | Min. | Typ. | Max. | |
| Q_C | Total capacitive charge | $V_R=400V$ $T_j=25^{\circ}C$ $Q_c = \int_0^{V_R} C(V)dV$ | | 17 | | nC |
| C | Total capacitance | $V_R=1V$ $f=1MHz$ $V_R=300V$ $f=1MHz$ $V_R=600V$ $f=1MHz$ | | 271 30.1 29.8 | | pF |
| E_C | Capacitance stored energy | $V_R=400V$ | | 4.5 | | μJ |

Typical Performance

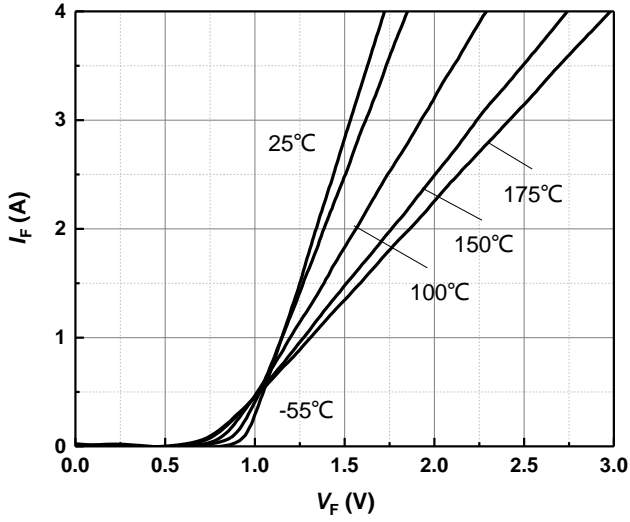


Figure 1. Typical forward characteristics

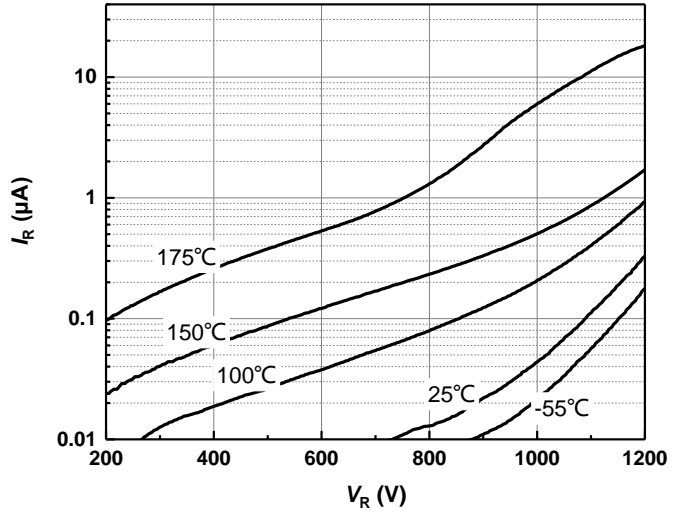


Figure 2. Typical reverse current as function of reverse voltage

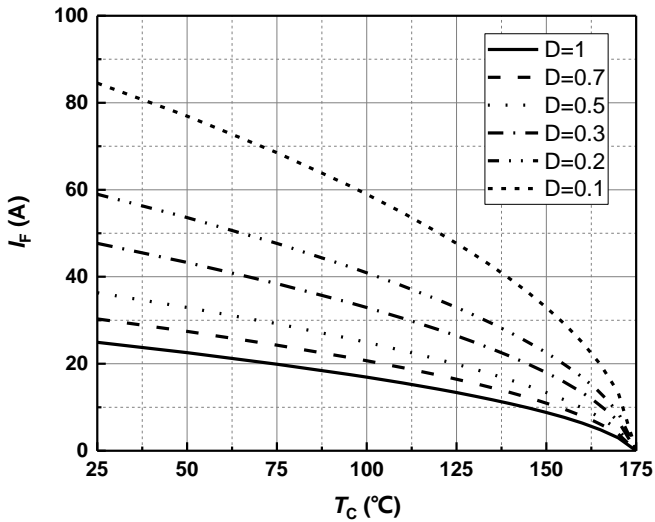


Figure 3. Diode forward current as function of temperature, D=duty cycle

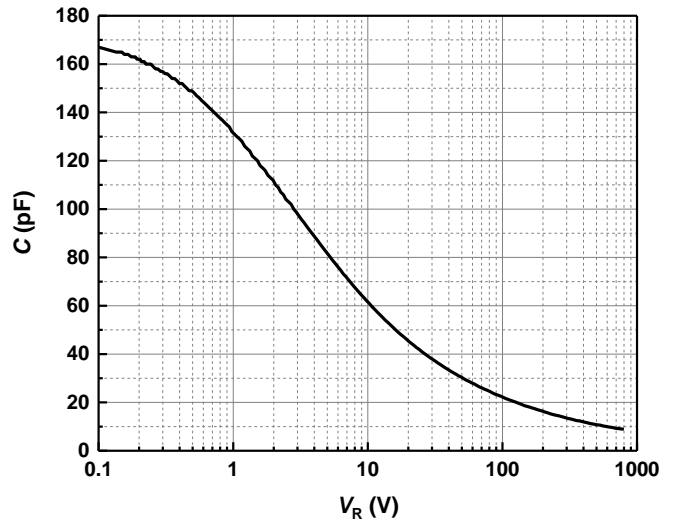


Figure 4. Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_J=25^\circ\text{C}$; $f=1\text{ MHz}$

Typical Performance

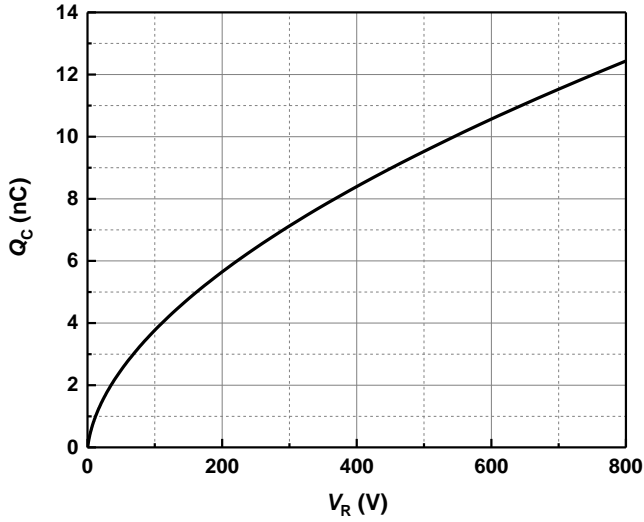


Figure 5. Typical reverse charge as function of reverse voltage

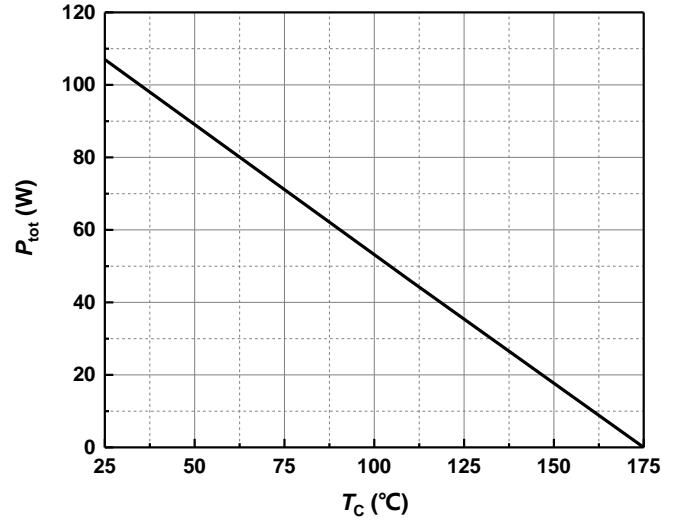


Figure 6. Power dissipation as function of case temperature

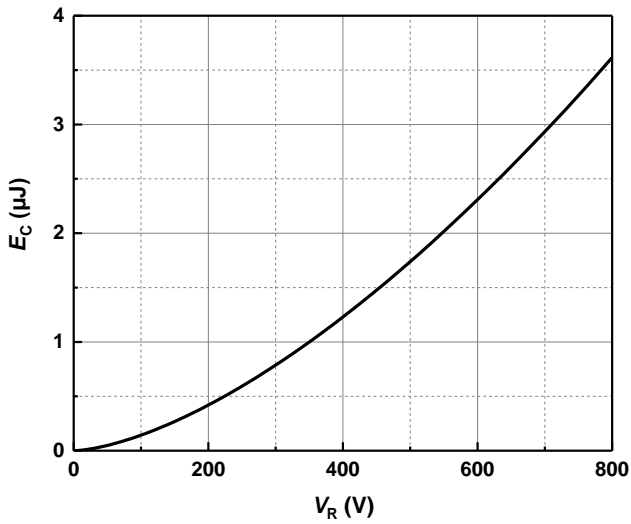


Figure 7. Capacitance stored energy

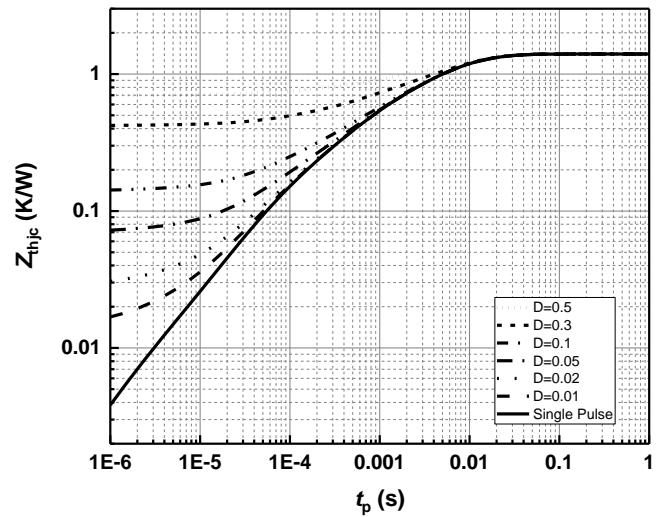
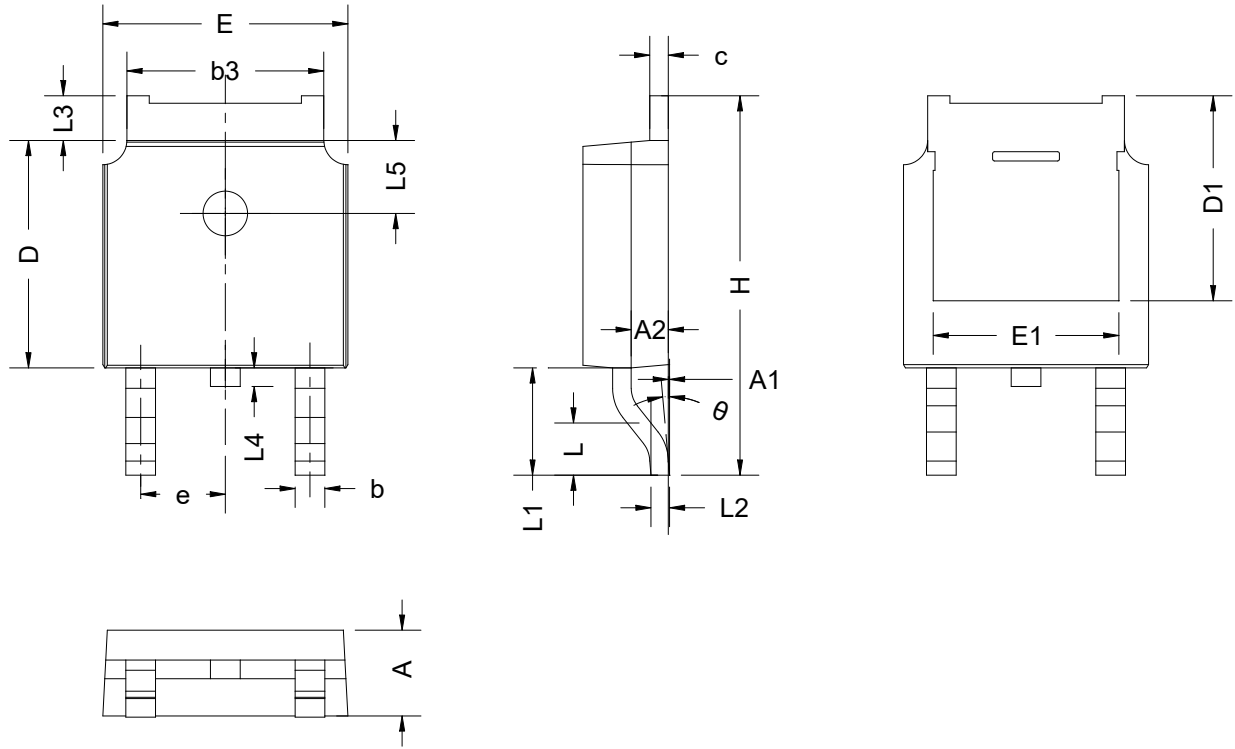


Figure 8. Max. transient thermal impedance, $Z_{thjc} = f(t)$, parameter: $D = t / T$

Package Dimensions


| SYMBOL | mm | | |
|----------|-----------|-------|-------|
| | MIN | NOM | MAX |
| A | 2.20 | 2.30 | 2.38 |
| A1 | 0.00 | - | 0.20 |
| A2 | 0.90 | 1.07 | 1.17 |
| b | 0.68 | 0.78 | 0.90 |
| b3 | 5.23 | 5.33 | 5.46 |
| c | 0.43 | 0.53 | 0.61 |
| D | 5.98 | 6.10 | 6.22 |
| D1 | 5.30 REF | | |
| E | 6.40 | 6.60 | 6.73 |
| E1 | 4.63 | - | - |
| e | 2.286 BSC | | |
| H | 9.40 | 10.10 | 10.50 |
| L | 1.38 | 1.50 | 1.75 |
| L1 | 2.90 REF | | |
| L2 | 0.51 BSC | | |
| L3 | 0.88 | - | 1.28 |
| L4 | 0.50 | - | 1.00 |
| L5 | 1.65 | 1.80 | 1.95 |
| θ | 0° | - | 8° |

Revision History

| Document Version | Date of Release | Description of Changes |
|-------------------------|------------------------|---------------------------------------|
| Rev. 0.1 | 2021-01-26 | Release of the preliminary datasheet. |
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Shenzhen, China
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